

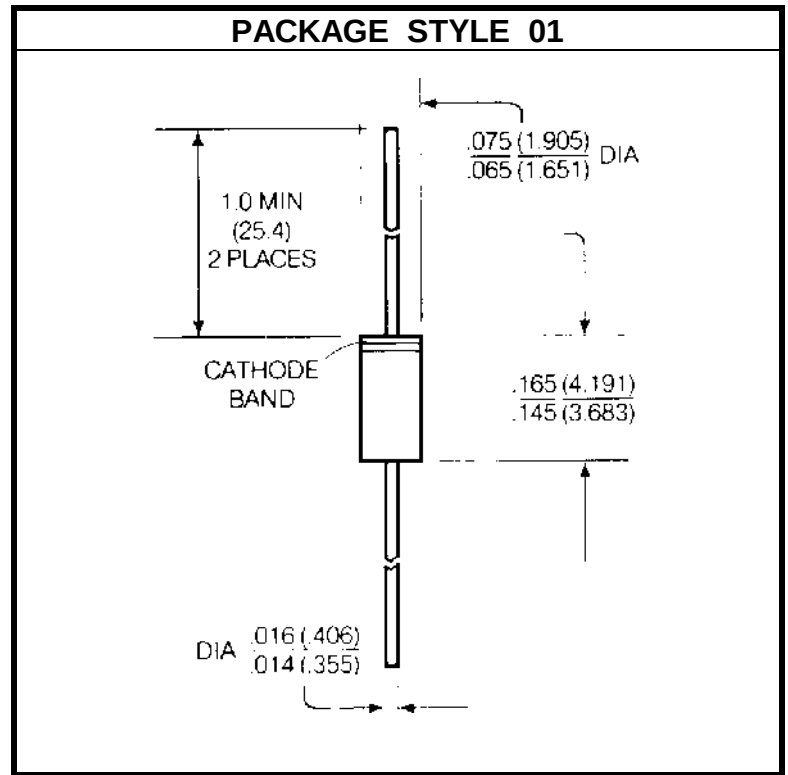
SILICON PIN DIODE

DESCRIPTION:

The **1N5719** is a Silicon PIN Diode Designed for General Purpose Attenuator and Switching Applications from 100 MHz to 3 GHz.

MAXIMUM RATINGS

I_F	100 mA
V_R	150 V
P_{DISS}	250 mW @ $T_A = 25\text{ }^{\circ}\text{C}$
T_J	$-65\text{ }^{\circ}\text{C}$ to $+200\text{ }^{\circ}\text{C}$
T_{STG}	$-65\text{ }^{\circ}\text{C}$ to $+200\text{ }^{\circ}\text{C}$
θ_{JC}	$0.7\text{ }^{\circ}\text{C/mW}$



CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{BR}	$I_R = 10\text{ }\mu\text{A}$	150			V
C_T	$V_R = 100\text{ V}$ $f = 1.0\text{ MHz}$			0.3	pF
R_S	$I_F = 100\text{ mA}$ $f = 100\text{ MHz}$			1.25	Ω
τ	$I_F = 50\text{ mA}$ $I_R = 250\text{ mA}$	100			μS
t_{rr}	$V_R = 10\text{ V}$ $f = 20\text{ mA}$		100		μS